

General Description

IGBT power module provides ultra low conduction loss as well as short circuit ruggedness. It is designed for applications such as general SMPS and UPS.

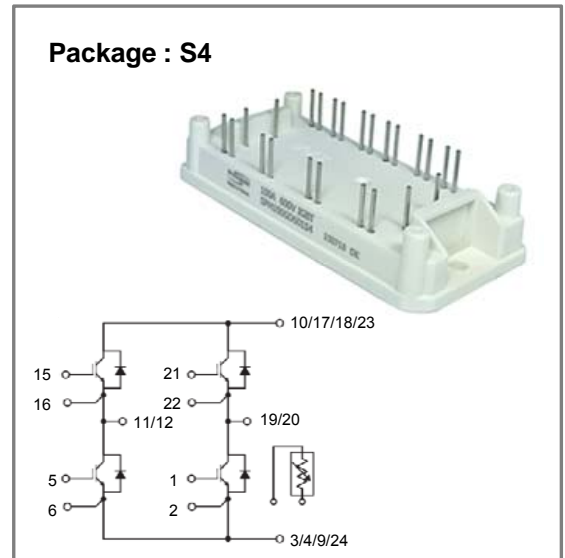
Features

- ✓ NPT Trench Technology
- ✓ Low Conduction Loss
- ✓ Fast & Soft inverse CAL Diodes
- ✓ Positive Temperature Coefficient
- ✓ Short Circuit Ruggedness
- ✓ $V_{CES}=600V$
- ✓ $I_C=100A$

Application

- ✓ Switching Mode Power Supplies(SMPS)
- ✓ High Power Inverter
- ✓ UPS, Robotics
- ✓ Electrical Welding Machine

preliminary data



Absolute Maximum Ratings ($T_C=25^{\circ}C$, unless otherwise noted.)

Symbol	Parameter	Conditions	Values	Units
V_{CES}	collector-emitter voltage	$V_{GE}=0, T_j \geq 25^{\circ}C$	600	V
V_{GES}	gate-emitter peak voltage	-	± 20	V
$I_{C(AV)}$	DC collector current	$T_C=80^{\circ}C$	100	A
I_{CRM}	repetitive peak collector current	$T_C=80^{\circ}C, t_p=1ms$	200	A
$I_{F(AV)}$	DC forward current	-	100	A
I_{FRM}	repetitive peak forw. current	10 ms, sin 180°	985	A
P_D	total power dissipation	$T_C=25^{\circ}C$	310	W
		$T_C=80^{\circ}C$	175	W
t_{SC}	short circuit withstand time	$V_{CC}=300V, V_{CES}=600V, V_{GE}=15V, T_j=125^{\circ}C$	10	μs
$T_{j(max)}$	maximum junction temperature	-	-40 ~ 150	$^{\circ}C$
T_{stg}	storage temperature	-	-40 ~ 125	$^{\circ}C$
V_{ISOL}	isolation test voltage	RMS, f=50Hz, t=1 minutes	2,500	V
Weight	module	-	40	g

Static Characteristics ($T_C=25^\circ\text{C}$, unless otherwise noted.)

Symbol	Parameter	min.	typ.	max.	Units	Conditions
BV_{CES}	collector-emitter breakdown voltage	600	-	-	V	$I_C=1\text{mA}$, $V_{GE}=0\text{V}$, $T_J=25^\circ\text{C}$
I_{CES}	collector-emitter cut-off current	-	-	1	mA	$V_{CE}=600\text{V}$, $V_{GE}=0\text{V}$
I_{GES}	gate-emitter Leakage Current	-500	-	500	nA	$V_{CE}=0\text{V}$, $V_{GE}=\pm 20\text{V}$
$V_{GE(th)}$	gate-emitter threshold voltage	6.0	7.5	9.0	V	$V_{GE}=V_{CE}$, $I_C=100\text{A}$
$V_{CE(SAT)}$	collector-emitter saturation voltage	-	2.2	2.6	V	$I_C=100\text{A}$, $V_{GE}=15\text{V}$, $T_C=25^\circ\text{C}$
		-	2.7	-	V	$I_C=100\text{A}$, $V_{GE}=15\text{V}$, $T_C=125^\circ\text{C}$
R_{Gint}	internal gate resistance	-	2.5	-	Ω	

Electrical Characteristics ($T_C=25^\circ\text{C}$, unless otherwise noted.)

Symbol	Parameter	min.	typ.	max.	Units	Conditions
$t_{d(on)}$	turn-on delay time	-	70	-	ns	$V_{DC}=300\text{V}$, $I_C=100\text{A}$, $R_G=15\Omega$, $V_{GE}=\pm 15\text{V}$, $L=60\text{ nH}$, Inductive Load, $T_J=25^\circ\text{C}$
t_r	rise time	-	40	-	ns	
$t_{d(off)}$	turn-off delay time	-	250	-	ns	
t_f	fall time	-	24	45	ns	
E_{ON}	turn-on switching loss	-	TBD	-	mJ	
E_{OFF}	turn-off switching Loss	-	2.1	2.6	mJ	
$t_{d(on)}$	turn-on delay time	-	65	-	ns	$V_{DC}=300\text{V}$, $I_C=100\text{A}$, $R_G=15\Omega$, $V_{GE}=\pm 15\text{V}$, $L=60\text{ nH}$, Inductive Load, $T_J=125^\circ\text{C}$
t_r	rise time	-	45	-	ns	
$t_{d(off)}$	turn-off delay time	-	255	-	ns	
T_f	fall time	-	30	56	ns	
E_{ON}	turn-on switching loss	-	TBD	-	mJ	
E_{OFF}	turn-off switching loss	-	2.5	3.1	mJ	
Q_g	total gate charge	-	450	-	nC	$V_{CE}=300\text{V}$, $I_C=100\text{A}$, $V_{GE}=\pm 15\text{V}$
C_{ies}	input capacitance	-	12	-	nF	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$ $f=1\text{MHz}$
C_{oes}	output capacitance	-	0.8	-	nF	
C_{res}	reverse transfer capacitance	-	0.3	-	nF	

Electrical Characteristics of Diode

Symbol	Parameter	min.	typ.	max.	Units	Conditions
V _F	forward voltage	-	1.3	1.6	V	T _C = 25°C, I _F = 75A
		-	1.2	-	V	T _C = 125°C, I _F = 75A
I _{RM}	peak reverse recovery current	-	90	-	A	T _j =150°C, 100A, 300V, 1,500A/us
E _{rec}	reverse recovery current	-	2.02	-	mJ	
Q _{rr}	reverse recovery charge	-	11.1	-	μC	

Thermal Characteristics

Symbol	Parameter	min.	typ.	max.	Units	Conditions
Rth(j-c)	junction-to-case (IGBT)	-	-	0.40	K/W	
Rth(j-c)	junction-to-case (FRD)	-	-	0.65	K/W	
Rth(c-f)	case-to-heat sink (with thermal compound)	-	0.05	-	K/W	

Performance Curves

Fig. 1 Typical IGBT output characteristics ($T_C = 25^\circ\text{C}$)

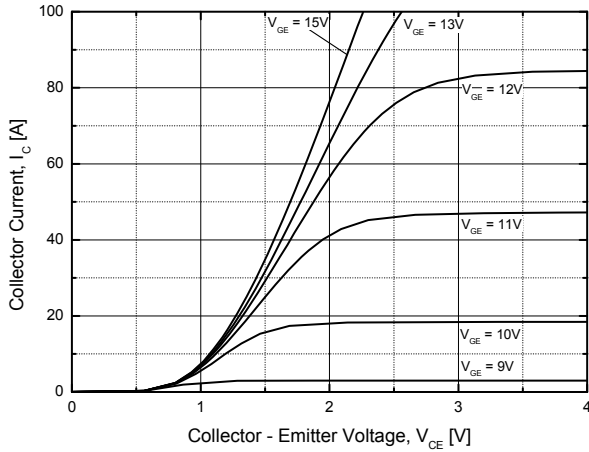


Fig. 2 Typical IGBT output characteristics ($T_C = 125^\circ\text{C}$)

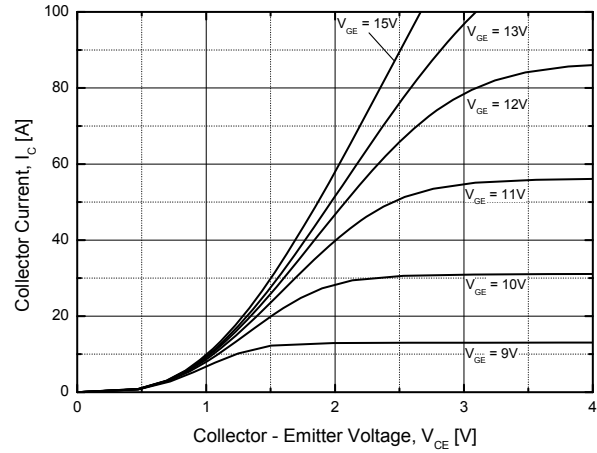


Fig. 3 Typical IGBT output characteristics, $V_{CE(SAT)}$

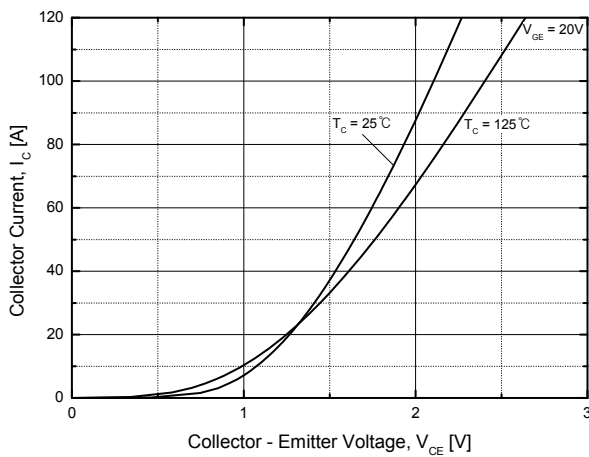


Fig. 4 Typical diode forward characteristics

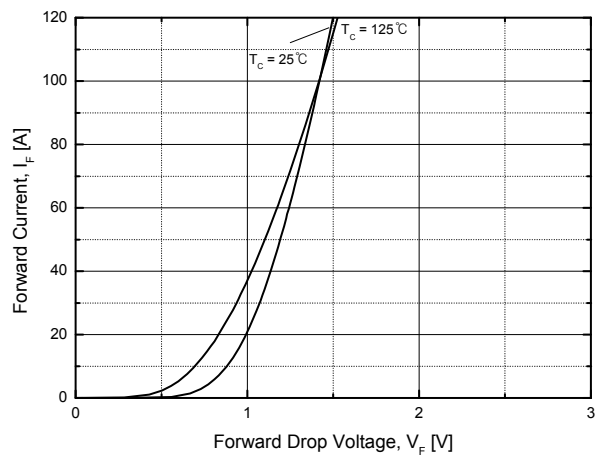


Fig. 5 Typical Capacitance

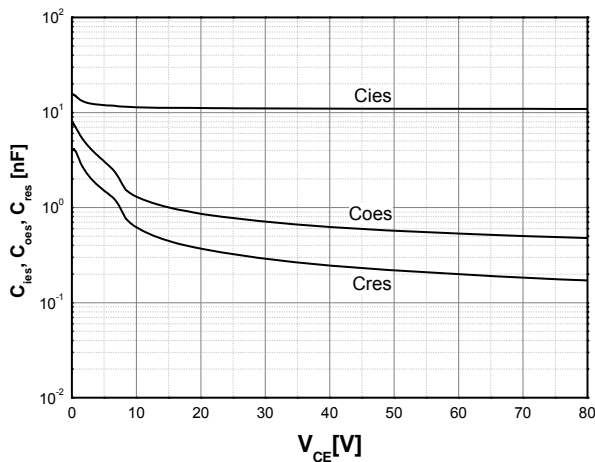
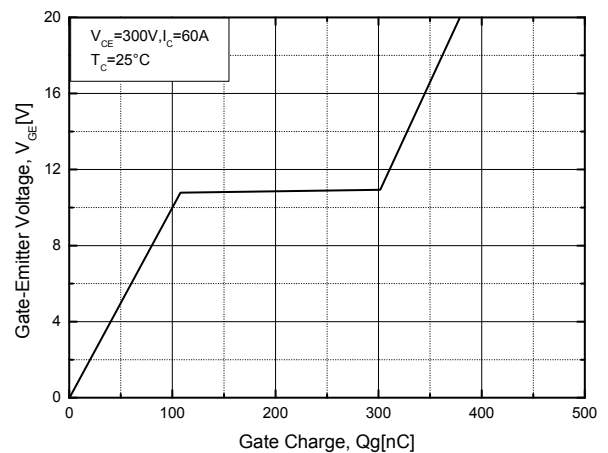
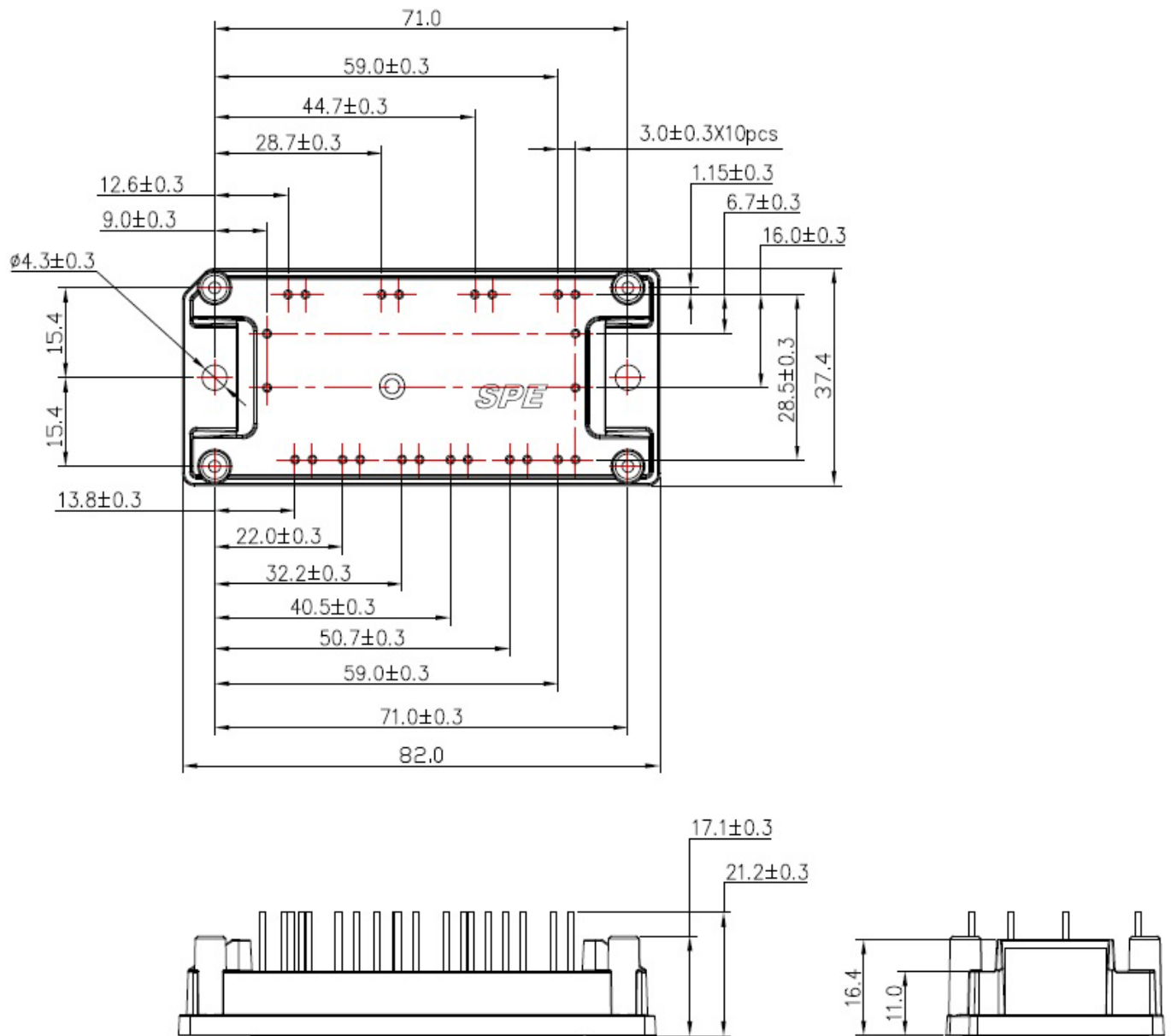


Fig. 6 Typical gate charge characteristics



Package Outline (Dimension in mm)



* Technical information on this specification subject to change without any notice.